



SPP9435

P-Channel Enhancement Mode MOSFET

DESCRIPTION

The SPP9435 is the P-Channel logic enhancement mode power field effect transistors are produced using high cell density , DMOS trench technology.

This high density process is especially tailored to minimize on-state resistance.

These devices are particularly suited for low voltage application , notebook computer power management and other battery powered circuits where high-side switching .

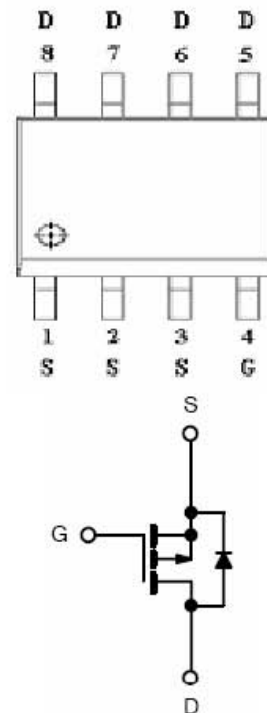
FEATURES

- ◆ $-30V/-5.7A, R_{DS(ON)} = 60m\Omega @ V_{GS} = -10V$
- ◆ $-30V/-5.0A, R_{DS(ON)} = 70m\Omega @ V_{GS} = -6V$
- ◆ $-30V/-4.4A, R_{DS(ON)} = 80m\Omega @ V_{GS} = -4.5V$
- ◆ Super high density cell design for extremely low RDS (ON)
- ◆ Exceptional on-resistance and maximum DC current capability
- ◆ SOP – 8P package design

APPLICATIONS

- Power Management in Note book
- Portable Equipment
- Battery Powered System
- DC/DC Converter
- Load Switch
- DSC
- LCD Display inverter

PIN CONFIGURATION(SOP – 8P)



PART MARKING





SPP9435

P-Channel Enhancement Mode MOSFET

PIN DESCRIPTION

Pin	Symbol	Description
1	S	Source
2	S	Source
3	S	Source
4	G	Gate
5	D	Drain
6	D	Drain
7	D	Drain
8	D	Drain

ORDERING INFORMATION

Part Number	Package	Part Marking
SPP9435S8RG	SOP- 8P	SPP9435
SPP9435S8TG	SOP- 8P	SPP9435

※ SPP9435S8RG : 13" Tape Reel ; Pb – Free

※ SPP9435S8TG : Tube ; Pb – Free

ABSOLUTE MAXIMUM RATINGS

(TA=25°C Unless otherwise noted)

Parameter	Symbol	Typical	Unit
Drain-Source Voltage	V _{DSS}	-30	V
Gate –Source Voltage	V _{GSS}	±20	V
Continuous Drain Current(T _J =150°C)	I _D	TA=25°C	-6.8
		TA=70°C	-4.6
Pulsed Drain Current	I _{DM}	-30	A
Continuous Source Current(Diode Conduction)	I _S	-2.3	A
Power Dissipation	P _D	TA=25°C	2.8
		TA=70°C	1.8
Operating Junction Temperature	T _J	-55/150	°C
Storage Temperature Range	T _{STG}	-55/150	°C
Thermal Resistance-Junction to Ambient	R _{θJA}	70	°C/W



SPP9435

P-Channel Enhancement Mode MOSFET

ELECTRICAL CHARACTERISTICS

(T_A=25°C Unless otherwise noted)

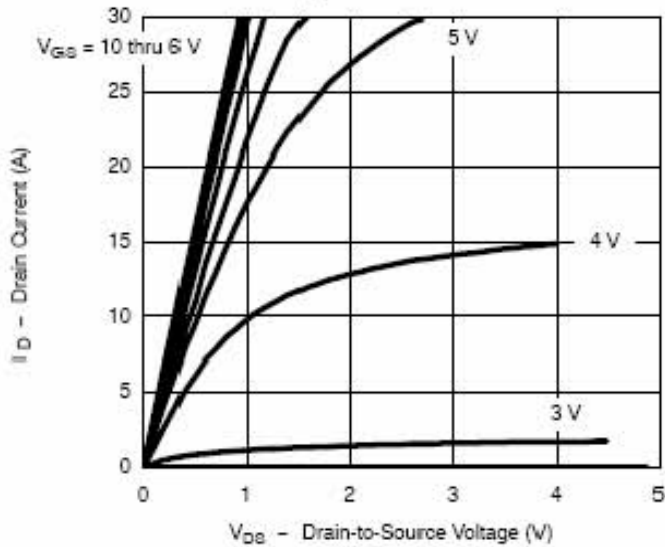
Parameter	Symbol	Conditions	Min.	Typ	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} =0V, I _D =-250uA	-30			V
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =-250uA	-1.0		-3.0	
Gate Leakage Current	I _{GSS}	V _{DS} =0V, V _{GS} =±20V			±100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =-24V, V _{GS} =0V			-1	uA
		V _{DS} =-24V, V _{GS} =0V T _J =85°C			-5	
On-State Drain Current	I _{D(on)}	V _{DS} = -5V, V _{GS} =-4.5V	-10			A
Drain-Source On-Resistance	R _{DSS(on)}	V _{GS} =-10V, I _D =-5.7A		0.048	0.060	Ω
		V _{GS} =-6.0V, I _D =-5.0A		0.054	0.070	
		V _{GS} =-4.5V, I _D =-4.4A		0.058	0.080	
Forward Transconductance	g _{fs}	V _{DS} =-15V, I _D =-5.7A		13		S
Diode Forward Voltage	V _{SD}	I _S =-2.3A, V _{GS} =0V		-0.8	-1.2	V
Dynamic						
Total Gate Charge	Q _g	V _{DS} =-15V, V _{GS} =-10V I _D = -3.5A		16	24	nC
Gate-Source Charge	Q _{gs}			2.3		
Gate-Drain Charge	Q _{gd}			4.5		
Input Capacitance	C _{iss}	V _{DS} =-15V, V _{GS} =0V f=1MHz		680		pF
Output Capacitance	C _{oss}			120		
Reverse Transfer Capacitance	C _{rss}			75		
Turn-On Time	t _{d(on)}	V _{DD} =-15V, R _L =15Ω I _D =-1.0A, V _{GEN} =-10V R _G =6Ω		14	25	nS
	t _r			15	26	
Turn-Off Time	t _{d(off)}			42	70	
	t _f			30	50	



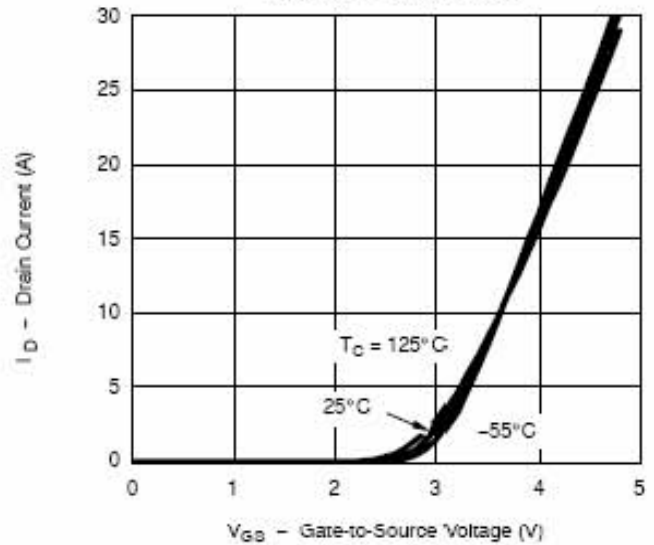
SPP9435 P-Channel Enhancement Mode MOSFET

TYPICAL CHARACTERISTICS

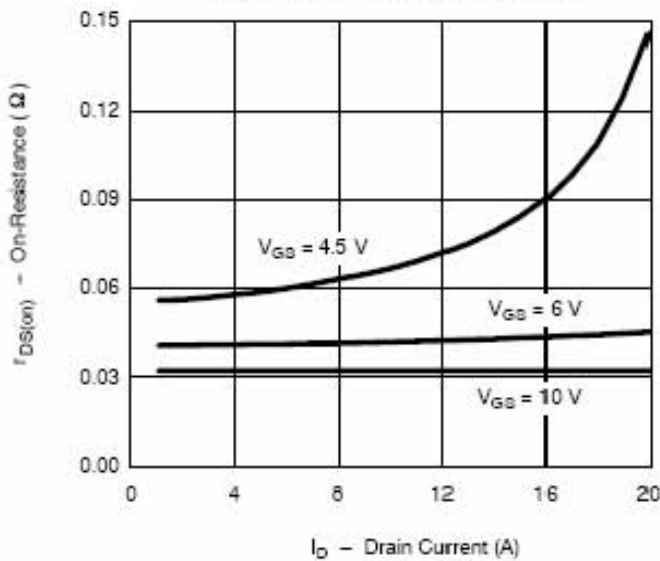
Output Characteristics



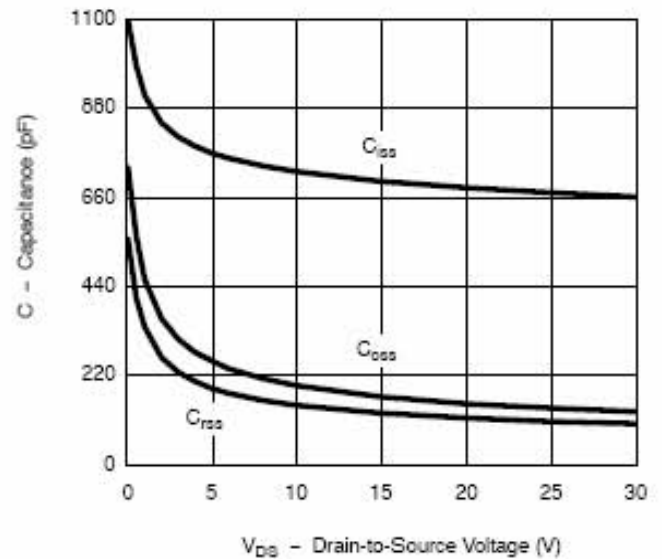
Transfer Characteristics



On-Resistance vs. Drain Current



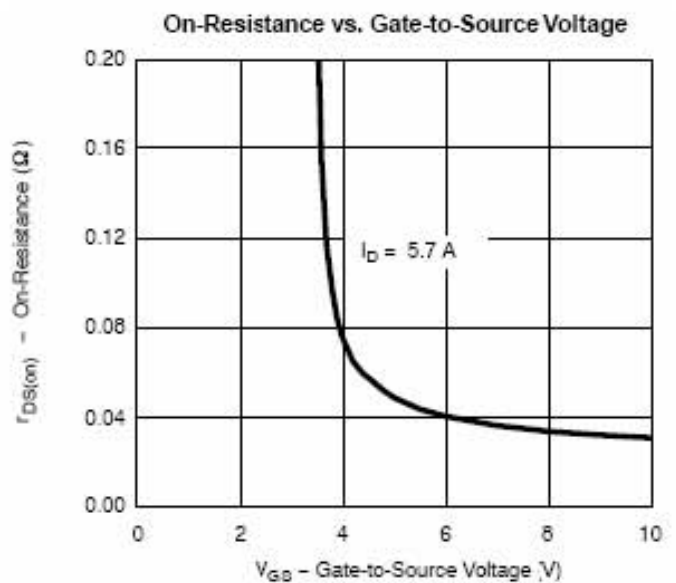
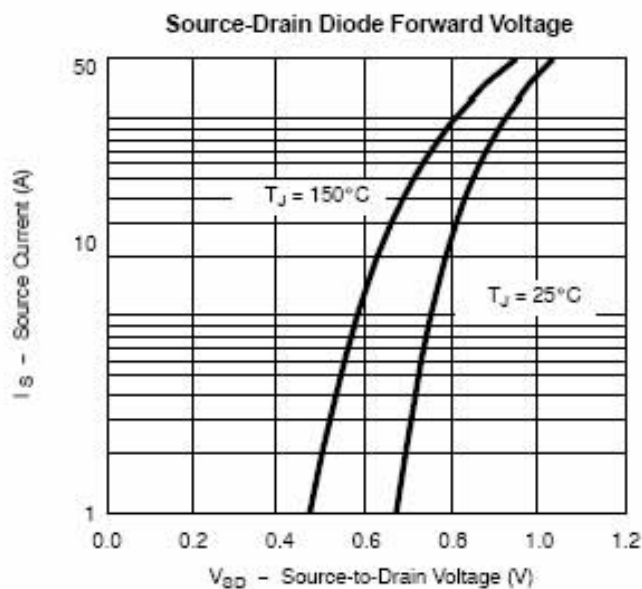
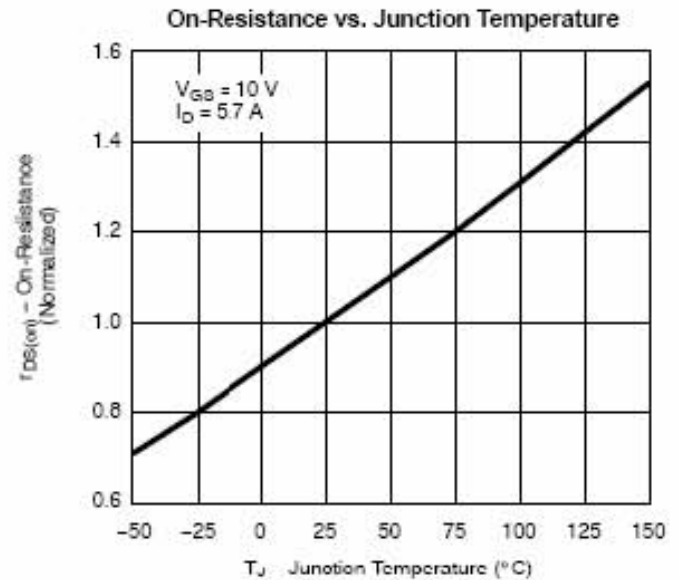
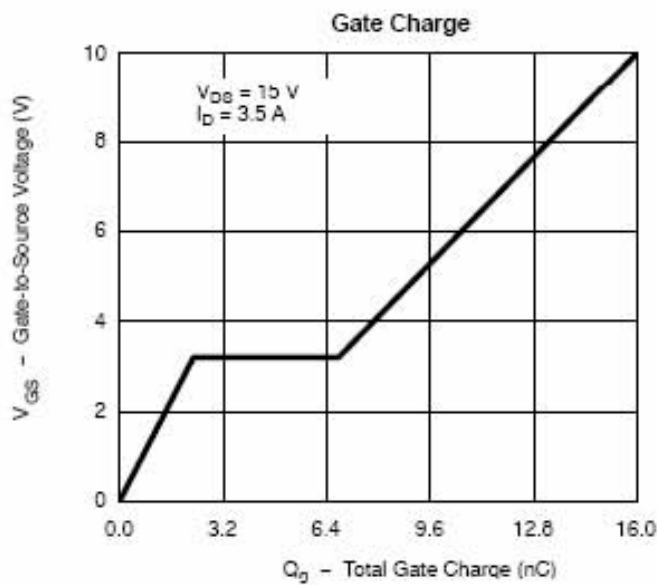
Capacitance





SPP9435 P-Channel Enhancement Mode MOSFET

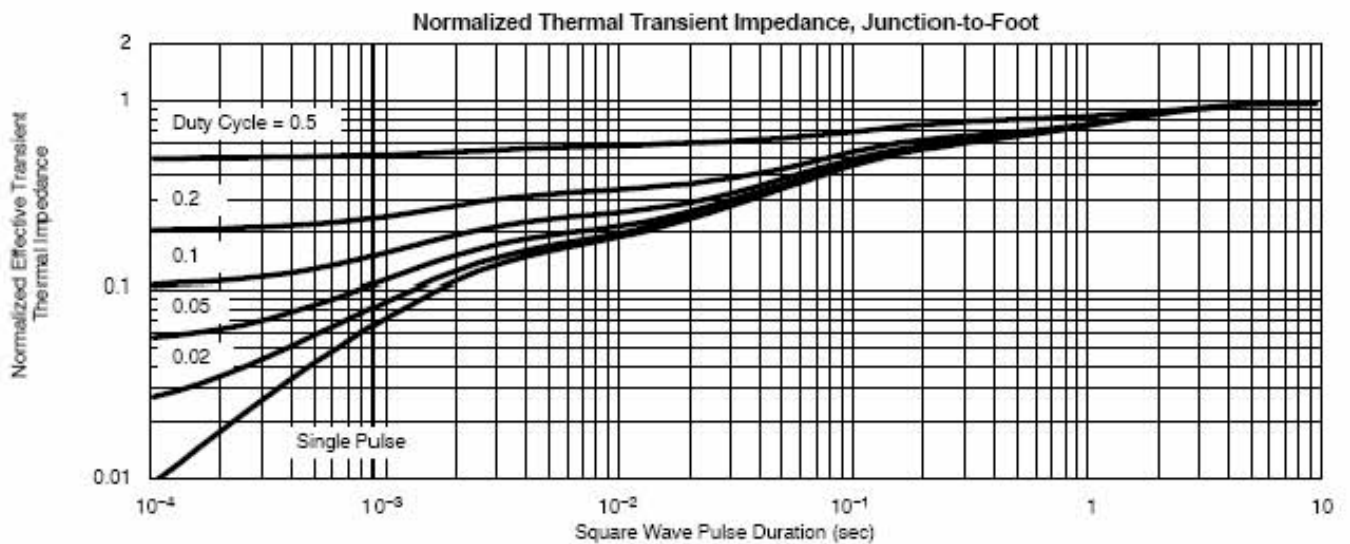
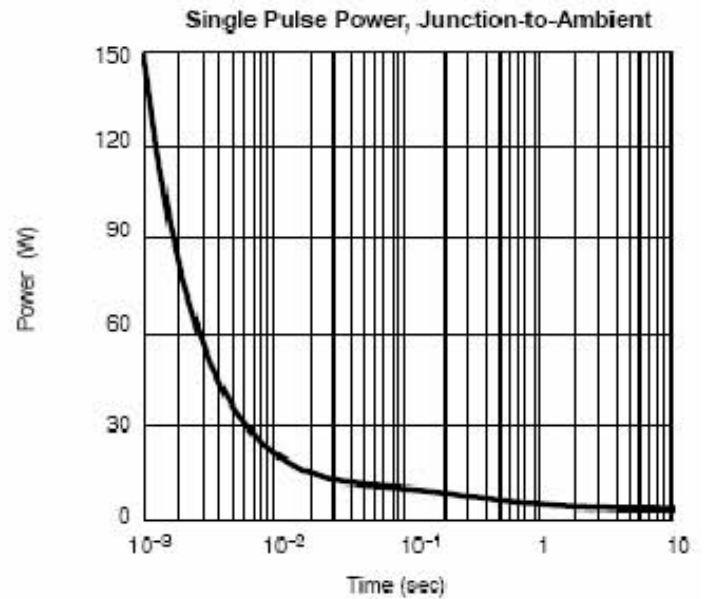
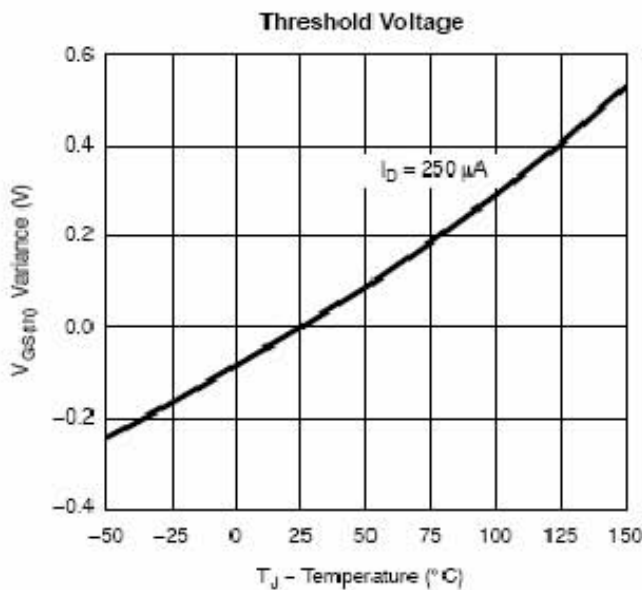
TYPICAL CHARACTERISTICS





SPP9435 P-Channel Enhancement Mode MOSFET

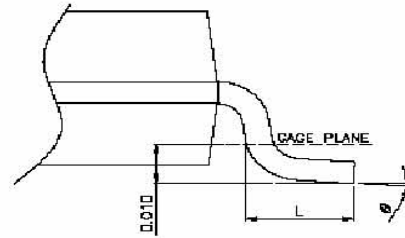
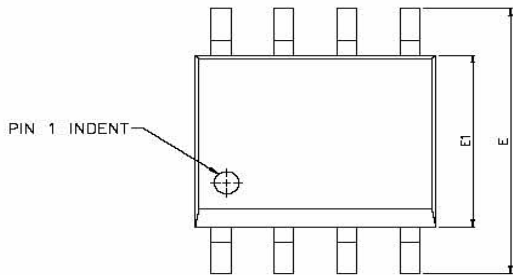
TYPICAL CHARACTERISTICS



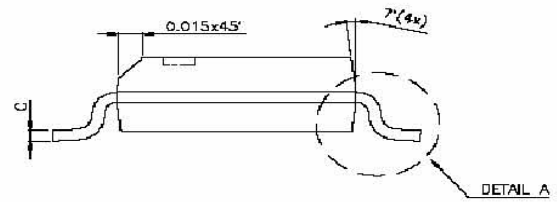
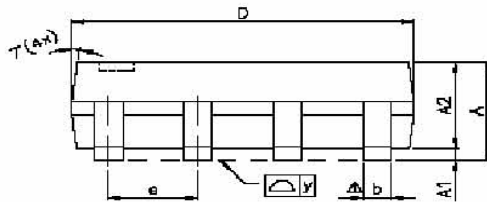


SPP9435 P-Channel Enhancement Mode MOSFET

SOP-8 PACKAGE OUTLINE



DETAIL A



SYMBOLS	DIMENSIONS IN MILLIMETERS			DIMENSIONS IN INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	1.47	1.60	1.73	0.058	0.063	0.068
A1	0.10	—	0.25	0.004	—	0.010
A2	—	1.45	—	—	0.057	—
b	0.33	0.41	0.51	0.013	0.016	0.020
C	0.19	0.20	0.25	0.0075	0.008	0.0098
D	4.80	4.85	4.95	0.189	0.191	0.195
E	5.80	6.00	6.20	0.228	0.236	0.244
E1	3.80	3.90	4.00	0.150	0.154	0.157
e	—	1.27	—	—	0.050	—
L	0.38	0.71	1.27	0.015	0.028	0.050
Δy	—	—	0.076	—	—	0.003
θ	0°	—	8°	0°	—	8°